

IRF1404-VB Datasheet

N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS}	40	V
$R_{DS(on)}$ $V_{GS} = 10$ V	3	m Ω
I_D	160	A
Configuration	Single	

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested

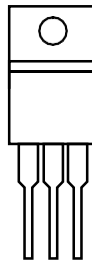


RoHS
COMPLIANT

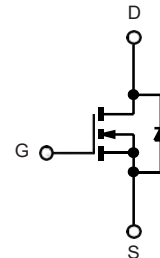
APPLICATIONS

- Synchronous Rectification
- Power Supplies

TO-220AB



G D S
Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	40	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	160 ^{a, c}	
		$T_C = 70$ °C	140 ^c	
		$T_A = 25$ °C	29 ^b	
		$T_A = 70$ °C	23 ^b	
Pulsed Drain Current	I_{DM}	350	mJ	
Avalanche Current Pulse	I_{AS}	80		
Single Pulse Avalanche Energy	E_{AS}	320		
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	110 ^{a, c}	
		$T_A = 25$ °C	2.6 ^b	
Maximum Power Dissipation	P_D	$T_C = 25$ °C	312 ^a	
		$T_C = 70$ °C	200	
		$T_A = 25$ °C	3.13 ^b	
		$T_A = 70$ °C	2.0 ^b	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	Steady State	R_{thJA}	32	40	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	0.33	0.4	

Notes:

a. Based on $T_C = 25$ °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. Calculated based on maximum junction temperature. Package limitation current is 110 A.

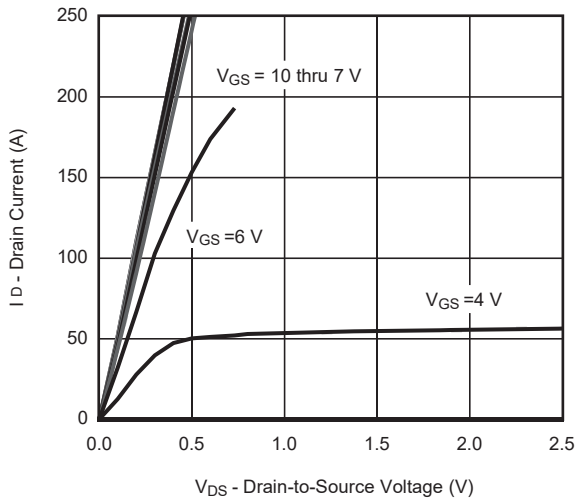
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		41		mV/°C	
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 8			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	μA	
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	120			A	
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		3		m Ω	
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		15			
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		180		S	
Dynamic^b							
Input Capacitance	C_{iss}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		5500		pF	
Output Capacitance	C_{oss}			650			
Reverse Transfer Capacitance	C_{rss}			450			
Total Gate Charge	Q_g	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		120		nC	
Gate-Source Charge	Q_{gs}			30			
Gate-Drain Charge	Q_{gd}			16			
Gate Resistance	R_g	$f = 1\text{ MHz}$		0.85	1.3	Ω	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 1.0\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		20	30	ns	
Rise Time	t_r			11	17		
Turn-Off Delay Time	$t_{d(off)}$			77	115		
Fall Time	t_f			10	15		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 1.0\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		102	155		
Rise Time	t_r			62	95		
Turn-Off Delay Time	$t_{d(off)}$			180	270		
Fall Time	t_f			60	90		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			110	A	
Pulse Diode Forward Current ^a	I_{SM}				200		
Body Diode Voltage	V_{SD}	$I_S = 20\text{ A}$		0.8	1.2	V	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		50	75	ns	
Body Diode Reverse Recovery Charge	Q_{rr}				70	105	nC
Reverse Recovery Fall Time	t_a				30		ns
Reverse Recovery Rise Time	t_b				20		

Notes:

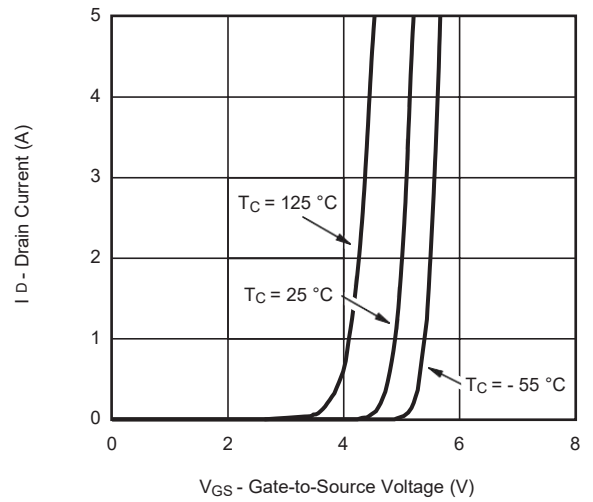
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

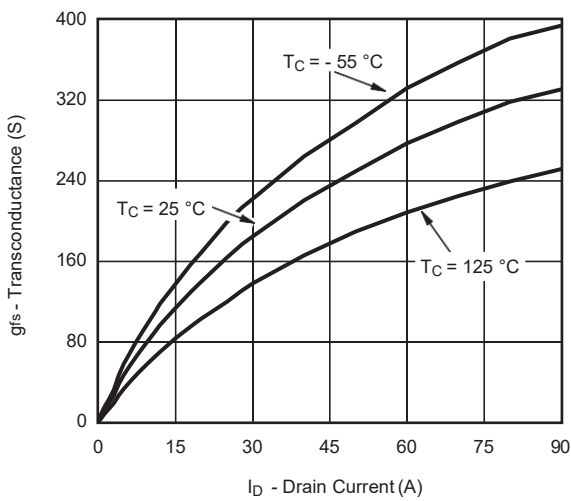
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



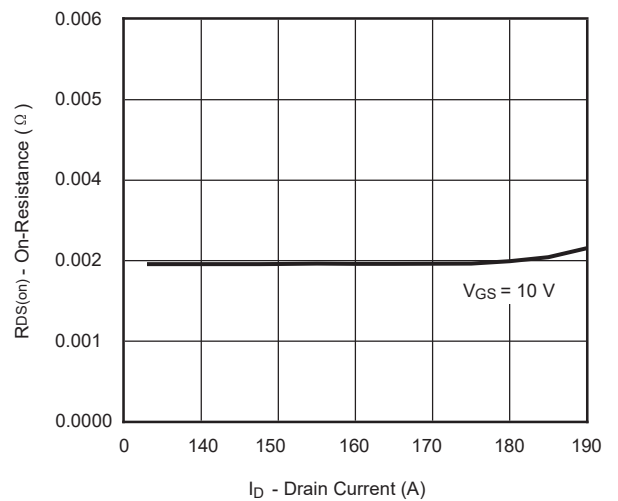
Output Characteristics



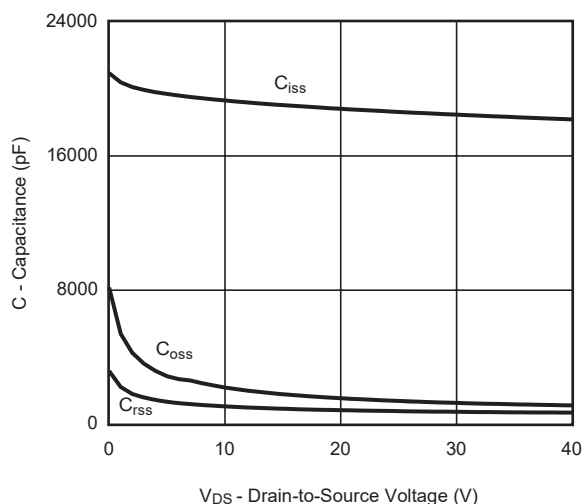
Transfer Characteristics



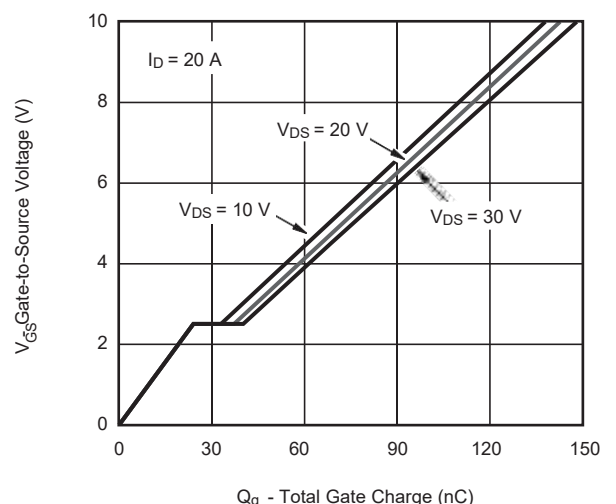
Transconductance



On-Resistance vs. Drain Current

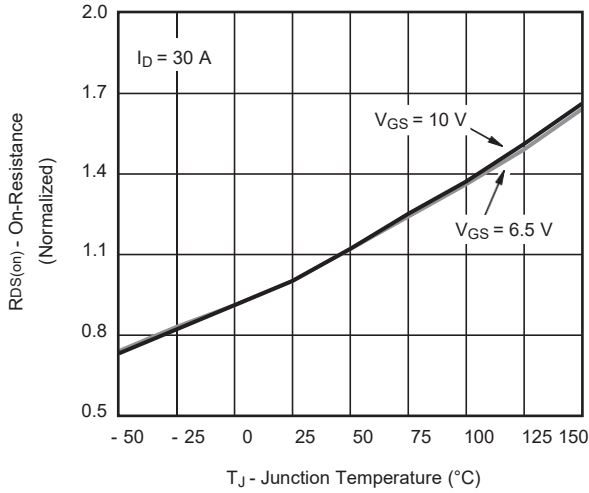


Capacitance

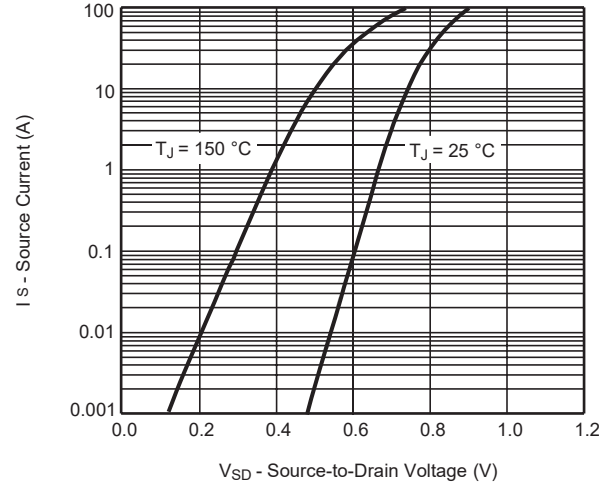


Gate Charge

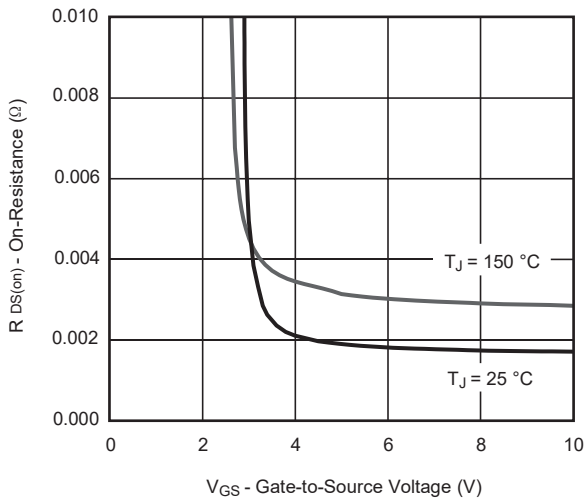
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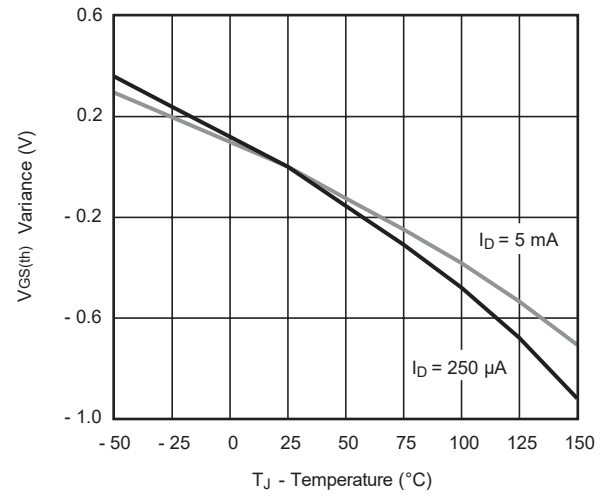
On-Resistance vs. Junction Temperature



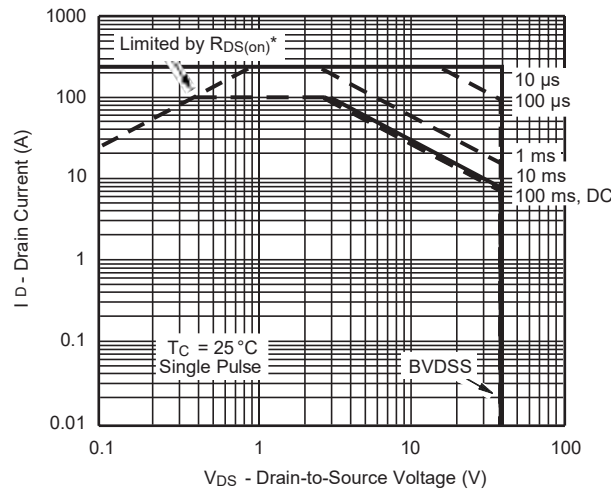
Forward Diode Voltage vs. Temperature



On-Resistance vs. Gate-to-Source Voltage



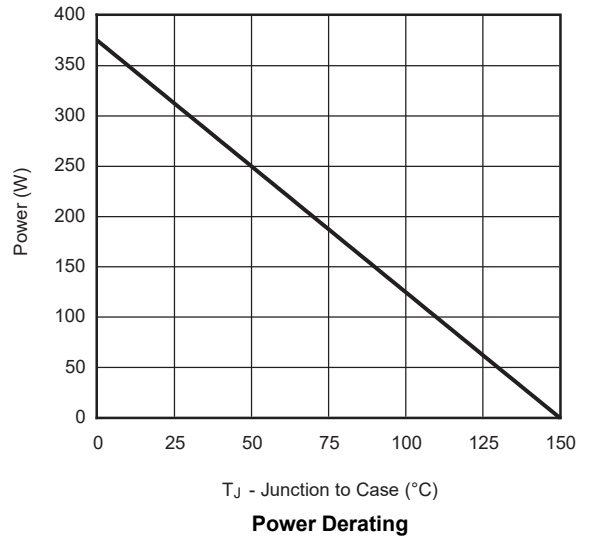
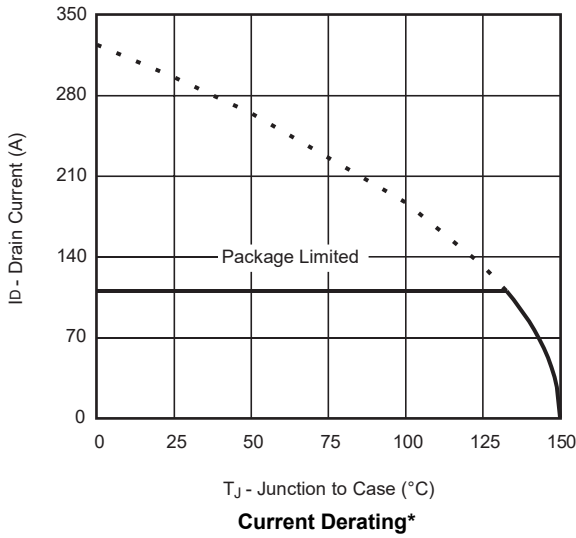
Threshold Voltage



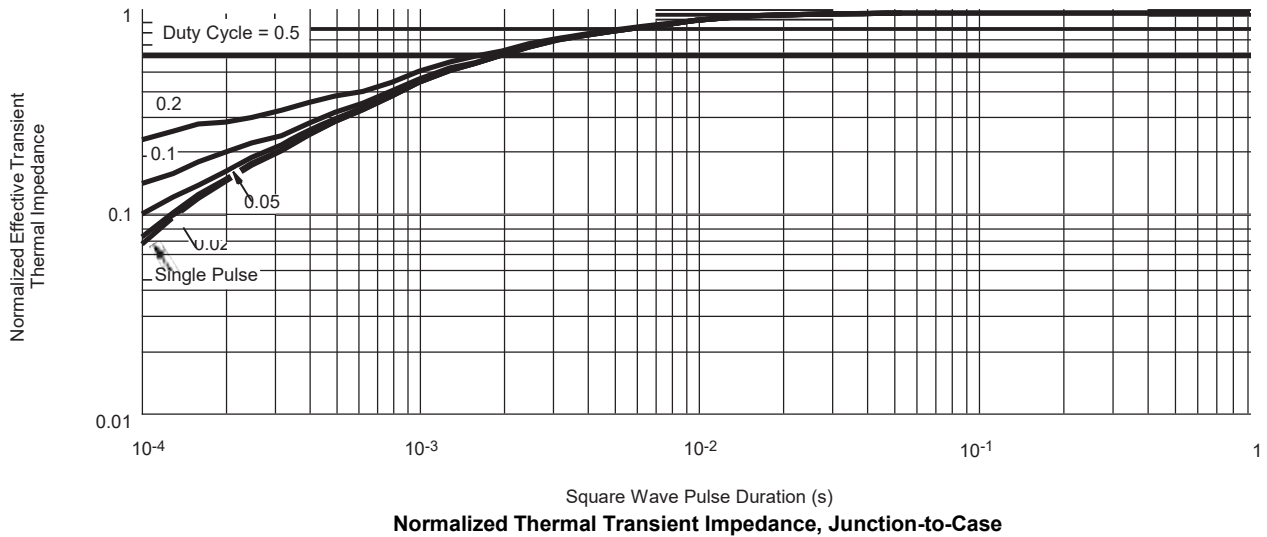
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

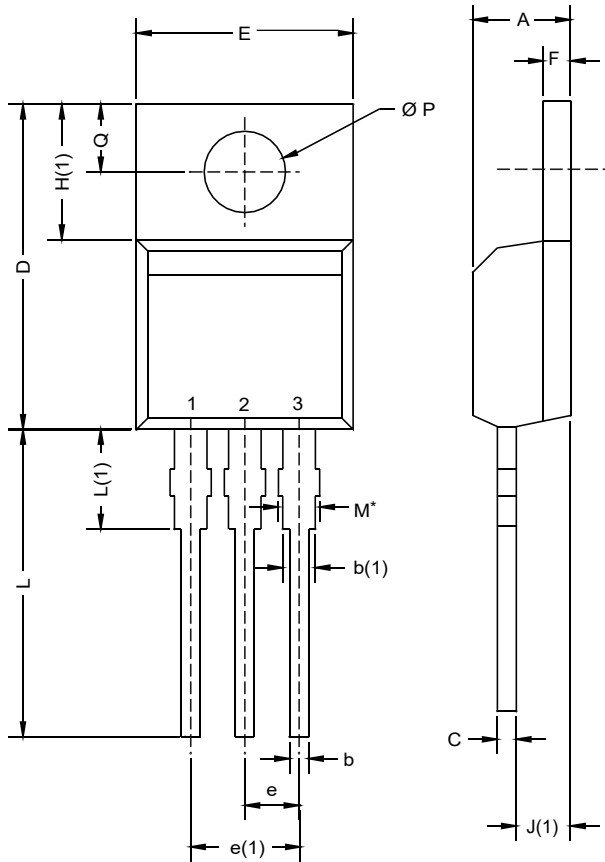
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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